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PAT-NO: JP409162416A

DOCUMENT-IDENTIFIER: JP 09162416 A

(IDS filed 7/2/7)

TITLE: SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

PUBN-DATE: June 20, 1997

INVENTOR-INFORMATION:

NAME

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NAME

COUNTRY

SEMICONDUCTOR ENERGY LAB CO LTD

N/A

APPL-NO: JP07346702

APPL-DATE: December 12, 1995

INT-CL (IPC): H01L029/786, H01L027/12, H01L021/336

ABSTRACT:

PROBLEM TO BE SOLVED: To provide a thin film transistor containing high characteristic by using metal element which promotes crystallization of silicon.

SOLUTION: Areas of codes 101 and 102, and areas of codes 108-110 are doped with nickel element selectively in the surface of an amorphous silicon film 103. And, by performing heat treatment, growth (horizontal growth) parallel to a substrate as shown with codes 104-107 is performed. At this time, the areas 108-110 whose width are made into 5 μ m or below act as stopper areas, so that the lateral growth from the areas 101 and 102 stop. In such a way, the horizontal growth area is provided by controlling. And a circuit such as a shift resistor, etc., can be constituted by areas provided with the same crystal growth form.

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